



**THE DATASHEET OF  
ZVN2120ASTOA**



Obsolete. A

**N-CHANNEL ENHANCEMENT  
MODE VERTICAL DMOS FET**

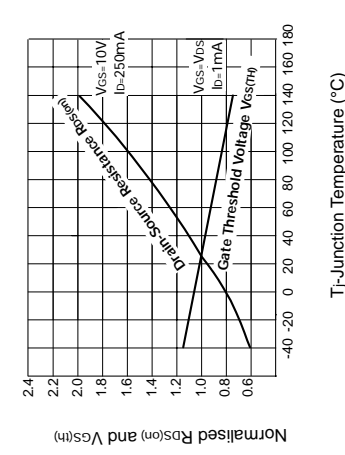
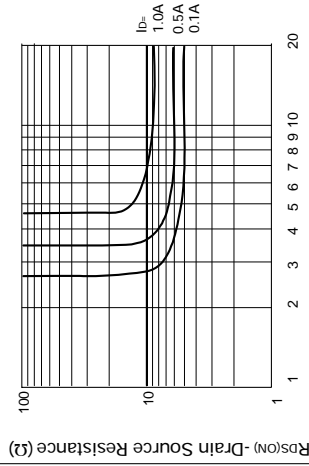
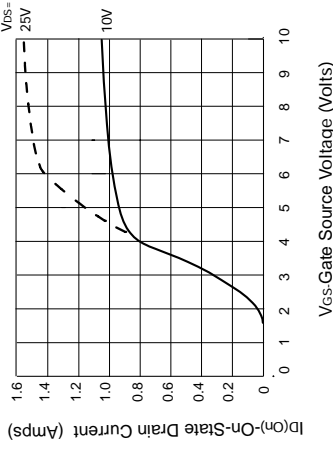
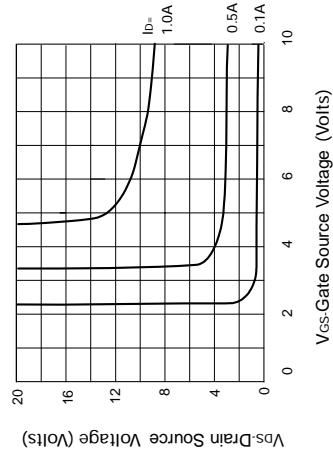
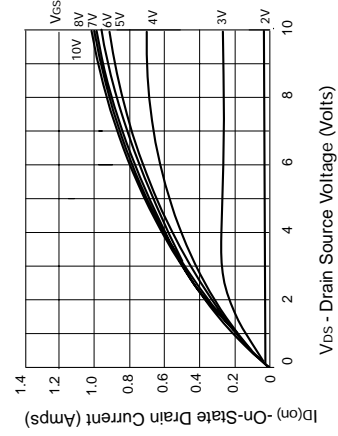
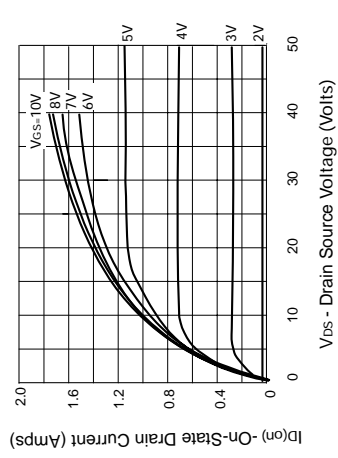
ISSUE 2 – MARCH 94

**FEATURES**

- \* 200 Volt  $V_{DS}$
- \*  $R_{DS(on)} = 10\Omega$

**ZVN2120A**

**TYPICAL CHARACTERISTICS**



**ABSOLUTE MAXIMUM RATINGS**

PARAMETER
Drain-Source Voltage
Continuous Drain Current at $T_{amb}=25^{\circ}C$
Pulsed Drain Current
Gate Source Voltage
Power Dissipation at $T_{amb}=25^{\circ}C$
Operating and Storage Temperature Range

**ELECTRICAL CHARACTERISTICS**

PARAMETER	SYMBOL
Drain-Source Breakdown Voltage	$BV_{DSS}$
Gate-Source Threshold Voltage	$V_{GS(th)}$
Gate-Body Leakage	$I_{GSS}$
Zero Gate Voltage Drain Current	$I_{DSS}$
On-State Drain Current (1)	$I_{D(on)}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$
Forward Transconductance (1)(2)	$g_{fs}$
Input Capacitance (2)	$C_{iss}$
Common Source Output Capacitance (2)	$C_{oss}$
Reverse Transfer Capacitance (2)	$C_{riss}$
Turn-On Delay Time (2)(3)	$t_{d(on)}$
Rise Time (2)(3)	$t_r$
Turn-Off Delay Time (2)(3)	$t_{d(off)}$
Fall Time (2)(3)	$t_f$

- (1) Measured under pulsed conditions. With  $V_{GS} = 10V$
- (2) Sample test.

# ZVN2120A

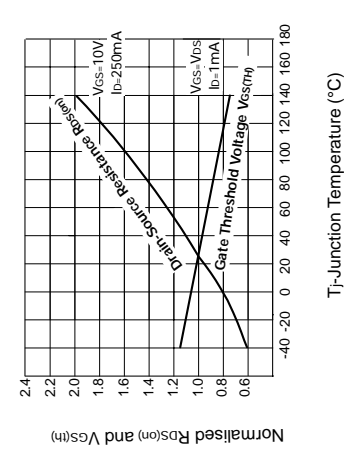
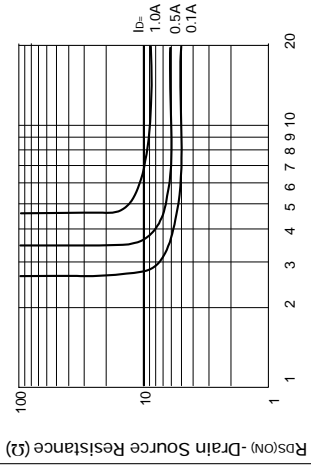
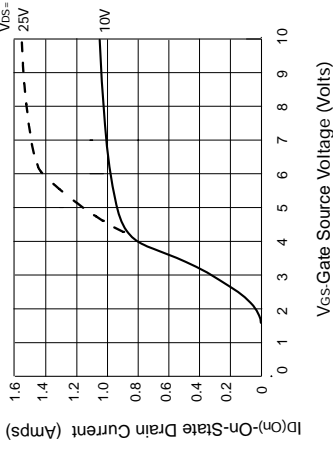
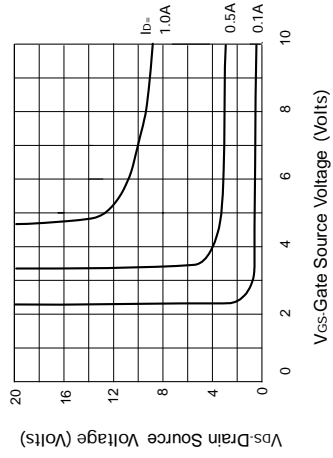
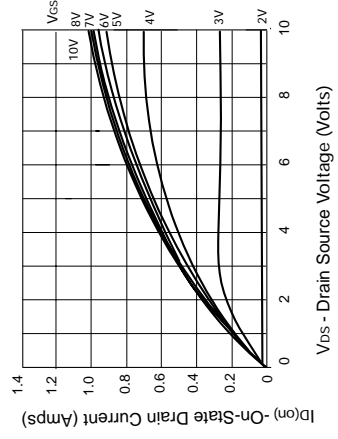
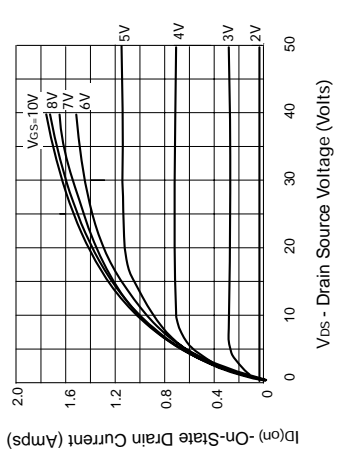
## N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 – MARCH 94

### FEATURES

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### TYPICAL CHARACTERISTICS



### ABSOLUTE MAXIMUM RATINGS

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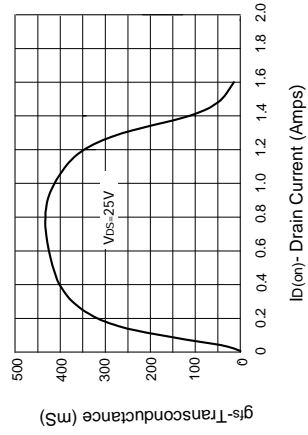
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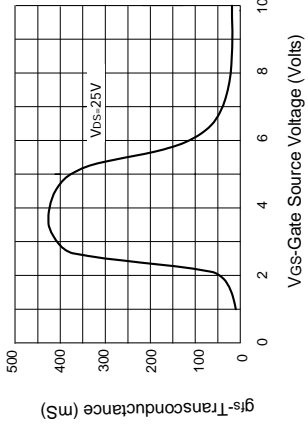
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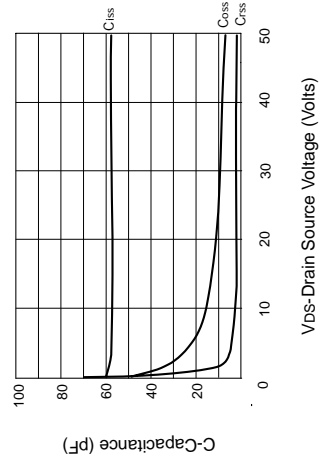
## TYPICAL CHARACTERISTICS



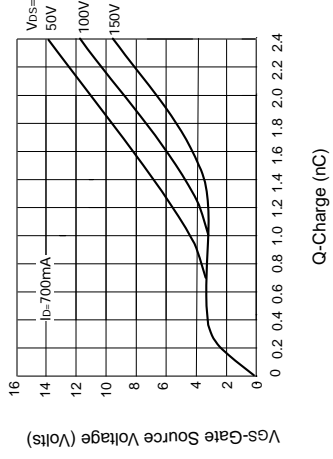
**Transconductance v drain current**



**Transconductance v gate-source voltage**



**Capacitance v drain-source voltage**



**Gate charge v gate-source voltage**

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